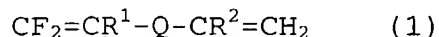


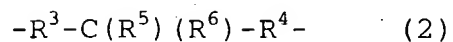
WHAT IS CLAIMED IS:

1. A resist composition comprising a fluoropolymer (A) which is a fluoropolymer having repeating units formed by cyclopolymerization of a fluorinated diene represented by the formula (1) and which has blocked acidic groups, provided that in a case where Q is a bivalent organic group having a group which can be converted to a blocked acidic group, said group is converted to a blocked acidic group after the cyclopolymerization, an acid-generating compound (B) which generates an acid under irradiation with light, and an organic solvent (C):



wherein each of R^1 and R^2 which are independent of each other, is a hydrogen atom, a fluorine atom, a methyl group or a trifluoromethyl group, and Q is a bivalent organic group having a blocked acidic group capable of forming an acidic group by an acid or a group which can be converted to such a blocked acidic group.

- ~~2. The resist composition according to Claim 1, wherein Q is a bivalent organic group represented by the formula (2):~~

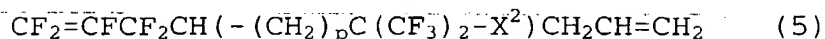
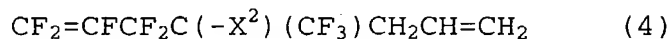


wherein each of R^3 and R^4 which are independent of each other, is a single bond, an oxygen atom, an alkylene group having at most 3 carbon atoms, which may have an etheric oxygen atom, or a fluoroalkylene group having at most 3 carbon atoms, which may have an etheric oxygen

atom, R^5 is a hydrogen atom, a fluorine atom, an alkyl group having at most 3 carbon atoms or a fluoroalkyl group having at most 3 carbon atoms, and R^6 is a blocked acidic group, an acidic group, or a monovalent organic group having a blocked acidic group or an acidic group.

3. The resist composition according to Claim 1, wherein the acidic group is an acidic hydroxyl group, and the blocked acidic group is a blocked acidic hydroxyl group.

4. The resist composition according to Claim 1, wherein the fluorinated diene is a fluorinated diene represented by the formula (4) or (5):



wherein X^2 is $O(t-C_4H_9)$, OCH_2OCH_3 , $OCOO(t-C_4H_9)$,

$OCH(CH_3)OC_2H_5$ or a 2-tetrahydropyranyloxy group, and p is an integer of from 1 to 3.

5. The resist composition according to Claim 1, wherein the fluoropolymer (A) is a copolymer comprising repeating units formed by cyclopolymerization of a fluorinated diene represented by the formula (1) and repeating units formed by polymerization of other monomers, wherein the proportion of the repeating units formed by polymerization of other monomers is at most 30 mol%.

6. The resist composition according to Claim 1, which is a resist composition for exposure by ultraviolet rays having a wavelength of at most 200 nm.

7. The resist composition according to Claim 6, wherein

the ultraviolet rays having a wavelength of at most 200 nm are ArF excimer laser beams or F₂ excimer laser beams.

8. A process for forming a pattern, which comprises coating the resist composition as defined in Claim 1 on a substrate, then removing the organic solvent (C) to form a thin film of a resist comprising the fluoropolymer (A) and the acid-generating compound (B), and then irradiating the thin film with ultraviolet rays having a wavelength of at most 200 nm capable of generating an acid from the acid-generating compound (B) to form a pattern.

9. The process according to Claim 8, wherein the ultraviolet rays having a wavelength of at most 200 nm are ArF excimer laser beams or F₂ excimer laser beams.